

isc Thyristors

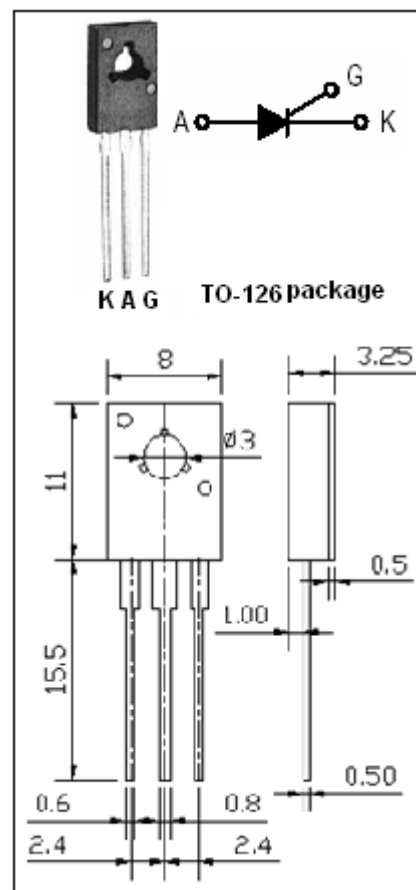
C106

FEATURES

- Glassivated surface for reliability and uniformity
- Practical level triggering and holding characteristics
- Designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	400	V
V_{RRM}	Repetitive peak off-state voltage	400	V
$I_{\text{T(AV)}}$	Average on-state current	2.5	A
$I_{\text{T(RMS)}}$	RMS on-state current	4	A
P_{GM}	Peak gate power	0.5	W
$P_{\text{G(AV)}}$	Average gate power	0.2	W
I_{TSM}	Non-repetitive peak on-state current	20	A
T_j	Operating junction temperature	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-40~+ 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_{\text{RRM}}=400\text{V}$ $V_{\text{RRM}}=400\text{V}, T_j=125^{\circ}\text{C}$		10 200	μA
I_{DRM}	Repetitive peak off-state current	$V_{\text{DRM}}=400\text{V}$ $V_{\text{DRM}}=400\text{V}, T_j=125^{\circ}\text{C}$		10 200	μA
I_{GT}	Gate trigger current	$V_D=6\text{V}; R_L=100\Omega, R_{\text{GK}}=1\text{K}\Omega$	10	200	μA
V_{TM}	On-state voltage	$I_T=8\text{A}$		1.75	V
I_{H}	Holding current	$V_D=24\text{V}, R_{\text{GK}}=1\text{K}\Omega, I_{\text{TM}}=4\text{A}$		5	mA
V_{GT}	Gate trigger voltage	$V_D=12\text{V}; R_L=100\Omega, R_{\text{GK}}=1\text{K}\Omega$		0.8	V